

Session Program

27 September 2026 to 2 October 2026

GADEST 2026

Silicon, germanium and their alloys II

GADEST 2026 - San Servolo Island, Venice (Italy)

Thursday 1 October

10:40

Silicon, germanium and their alloys II

Session | Location: Auditorium Hall

10:40-11:20

A theoretical perspective of defects in silicon and germanium: From nanoelectronics to quantum computing

11:20-11:40

Diffusion of p-type dopants in Germanium

Speakers

Bracht, Sinz

11:40-12:00

Shallow junction formation in silicon by laser annealing of phosphorus end-terminated polymers

Speaker

Gaetano Calogero

12:00-12:20

Modulation Acceptor Doping of Silicon: Induced defects in SiO₂ for hole generation in impurity-free Si

Speaker

Daniel Hiller

12:20-12:40

Beyond the Statistical Indeterminism of Ion Implantation: Toward Deterministic Nanoscale Doping and Defect Engineering

Speaker

Giuseppe D'Arrigo

12:40